

Sub
F/G1
Concl'd

a protective outer wall adjacent to the substrate;
an inner sealing wall located exclusively within the shallow region
and adjacent to the protective outer wall and
the shallow region having a shallow region cross-sectional area;
wherein the deep region cross-sectional area is greater the shallow
region cross-sectional area.

5. (Amended) A semiconductor isolation structure comprising:

Sub
G2

a substrate, the substrate comprising a surface;
a first device and a second device formed within the substrate;
an isolation region formed within the substrate between the first device and the
second device, the isolation region comprising:
a deep region which extends into the substrate, the deep region comprising
an oxide;
a single shallow region which extends to the surface of the substrate, the
shallow region comprising:
a protective outer wall adjacent to the substrate,
an inner sealing wall located exclusively within the shallow region
and adjacent to the protective outer wall.

A replacement copy of the claims is included following the Applicants' response.